

Silicon NPN Power Transistors

2SD2331

DESCRIPTION

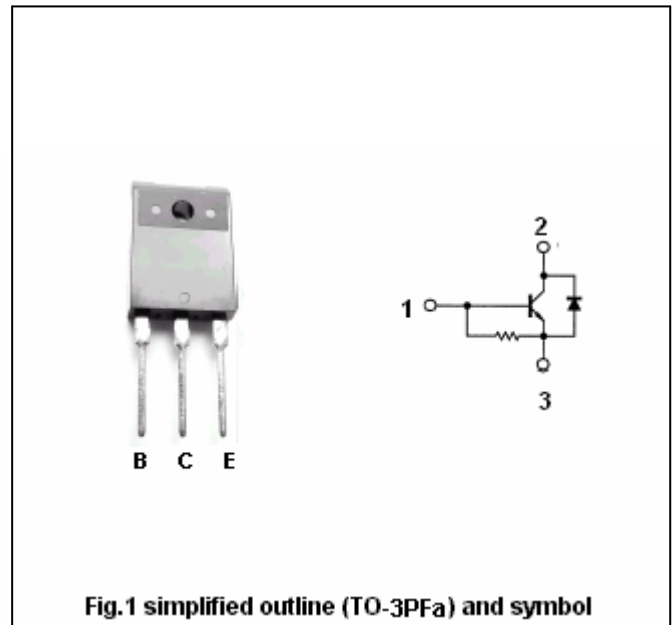
- With TO-3PFa package
- High voltage;high speed
- Built-in damper diode

APPLICATIONS

- For color TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage		5	V
I_C	Collector current		3.5	A
I_B	Base current		1	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	40	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=200mA$, $I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=3A$; $I_B=0.8A$		3.0	5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=3A$; $I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800V$ $I_E=0$			10	μA
h_{FE}	DC current gain	$I_C=0.5A$; $V_{CE}=5V$	8			
f_T	Transition frequency	$I_C=0.1A$; $V_{CE}=10V$		3		MHz
V_F	Diode forward voltage	$I_F=3.5A$			2.0	V

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PACKAGE OUTLINE

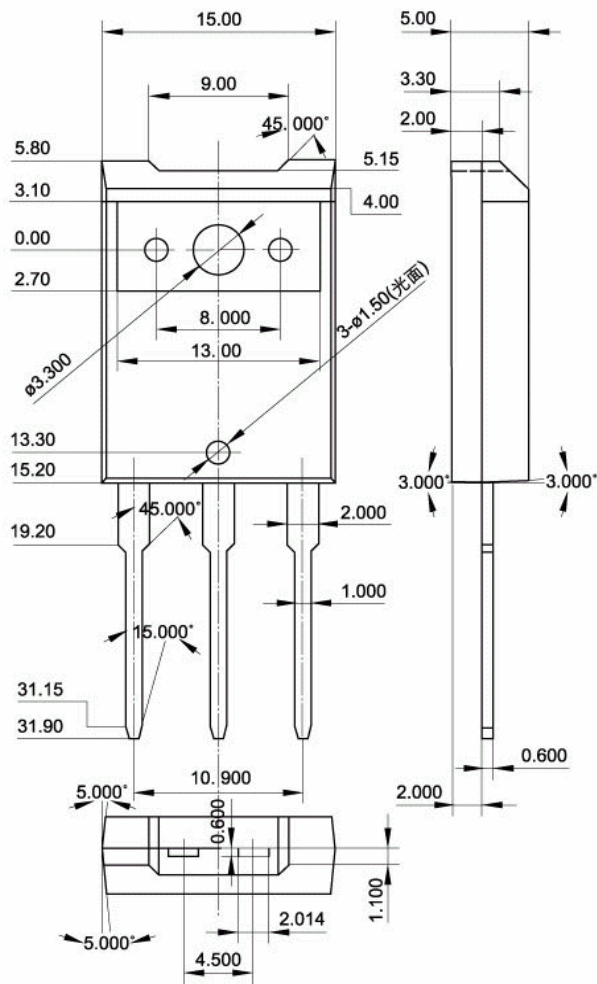


Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)